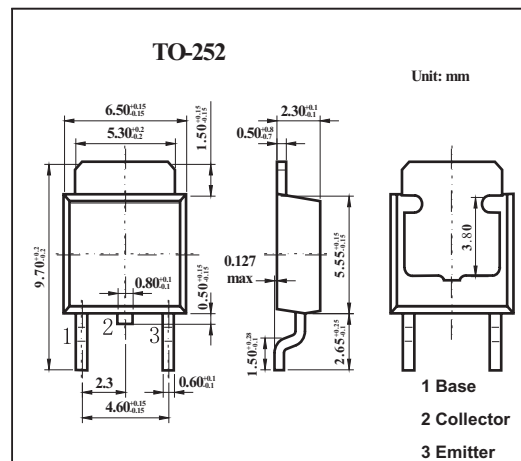


Silicon PNP Transistor

2SB768

■ Features

- High Voltage: $V_{CB0} = -150V$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-to-Base Voltage	V_{CB0}	-200	V
Collector-to-Emitter Voltage	V_{CEO}	-150	V
Emitter-to-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-2	A
Collector Current (Pulse) *1	I_{CP}	-3	A
Total Power Dissipation *2 $T_a = 25^\circ C$	P_T	2	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

*1 $PW \leq 10ms$, Duty Cycle $\leq 50\%$

*2 when mounted on ceramic substrate of $7.5cm^2 \times 0.7mm$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -150V, I_E = 0$			-50	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-50	μA
DC Current Gain *	h_{FE}	$V_{CE} = -10V, I_C = -0.4A$	40	80	200	
Collector-to-Emitter Saturation Voltage *	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.15	-1.0	V
Gain Bandwidth Product	f_T	$V_{CE} = -10V, I_E = -0.4mA$		10		MHz

* Pulsed : $pw \leq 350\mu s$, Duty Cycle $\leq 2\%$

■ h_{FE} Classification

Marking	M	L	K
h_{FE}	40 to 80	60 to 120	100 to 200